

HiPerFET™ Power MOSFETs

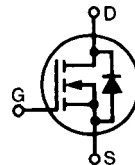
ISOPLUS247™

IXFR 26N50
IXFR 24N50

| V_{DSS} | I_{D25} | $R_{DS(on)}$ |
|-----------|-----------|---------------|
| 500 V | 24 A | 0.20 Ω |
| 500 V | 22 A | 0.23 Ω |

(Electrically Isolated Back Surface)

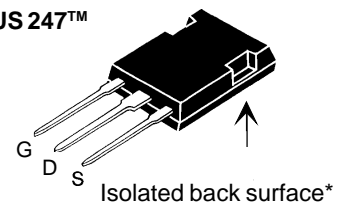
N-Channel Enhancement Mode
High dV/dt , Low t_{rr} , HDMOS™ Family



$t_{rr} \leq 250$ ns

| Symbol | Test Conditions | Maximum Ratings | |
|---------------|--|-----------------|------------------|
| V_{DSS} | $T_J = 25^\circ\text{C}$ to 150°C | 500 | V |
| V_{DGR} | $T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1$ M Ω | 500 | V |
| V_{GS} | Continuous | ± 20 | V |
| V_{GSM} | Transient | ± 30 | V |
| I_{D25} | $T_C = 25^\circ\text{C}$ | 26N50 | 26 A |
| | | 24N50 | 24 A |
| I_{DM} | $T_C = 25^\circ\text{C}$, Pulse width limited by T_{JM} | 26N50 | 104 A |
| | | 24N50 | 96 A |
| I_{AR} | $T_C = 25^\circ\text{C}$ | 26N50 | 26 A |
| | | 24N50 | 24 A |
| E_{AR} | $T_C = 25^\circ\text{C}$ | 30 | mJ |
| dv/dt | $I_S \leq I_{DM}$, $di/dt \leq 100$ A/ μs , $V_{DD} \leq V_{DSS}$ $T_J \leq 150^\circ\text{C}$, $R_G = 2$ Ω | 5 | V/ns |
| P_D | $T_C = 25^\circ\text{C}$ | 250 | W |
| T_J | | -55 ... +150 | $^\circ\text{C}$ |
| T_{JM} | | 150 | $^\circ\text{C}$ |
| T_{stg} | | -55 ... +150 | $^\circ\text{C}$ |
| T_L | 1.6 mm (0.062 in.) from case for 10 s | 300 | $^\circ\text{C}$ |
| V_{ISOL} | 50/60 Hz, RMS $t = 1$ minute leads-to-tab | 2500 | V~ |
| Weight | | 6 | g |

ISOPLUS 247™



G = Gate D = Drain
S = Source

* Patent pending

Features

- Silicon chip on Direct-Copper-Bond substrate
- High power dissipation
- Isolated mounting surface
- -2500V electrical isolation
- Low drain to tab capacitance (<50pF)
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Fast intrinsic Rectifier

Applications

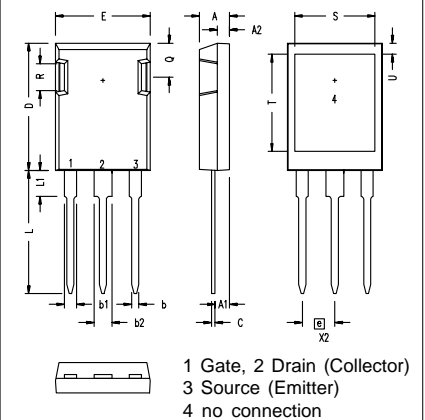
- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC motor control

Advantages

- Easy assembly
- Space savings
- High power density

| Symbol | Test Conditions | Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified) | | |
|--------------|--|---|------|---------------|
| | | min. | typ. | max. |
| V_{DSS} | $V_{GS} = 0$ V, $I_D = 250$ μA | 500 | | V |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 4$ mA | 2 | 4 | V |
| I_{GSS} | $V_{GS} = \pm 20$ V _{DC} , $V_{DS} = 0$ | | | ± 100 nA |
| I_{DSS} | $V_{DS} = 0.8 \cdot V_{DSS}$ $V_{GS} = 0$ V | $T_J = 25^\circ\text{C}$ | 200 | μA |
| | | $T_J = 125^\circ\text{C}$ | 1 | mA |
| $R_{DS(on)}$ | $V_{GS} = 10$ V, $I_D = I_T$ Notes 1 & 2 | 26N50 | 0.20 | Ω |
| | | 24N50 | 0.23 | Ω |

| Symbol | Test Conditions | Characteristic Values | | | |
|---------------------------|--|---|------|------|-----|
| | | (T _J = 25°C, unless otherwise specified) | | | |
| | | min. | typ. | max. | |
| g_{fs} | V _{DS} = 15 V; I _D = I _T Note 1 | 11 | 21 | S | |
| C_{iss} | V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz | | 4200 | pF | |
| C_{oss} | | | 450 | pF | |
| C_{riss} | | | 135 | pF | |
| t_{d(on)} | V _{GS} = 10 V, V _{DS} = 0.5 • V _{DSS} , I _D = I _T R _G = 1 Ω (External), | | 16 | 25 | ns |
| t_r | | | 33 | 45 | ns |
| t_{d(off)} | | | 65 | 80 | ns |
| t_f | | | 30 | 40 | ns |
| Q_{g(on)} | V _{GS} = 10 V, V _{DS} = 0.5 • V _{DSS} , I _D = I _T | | 135 | 160 | nC |
| Q_{gs} | | | 28 | 40 | nC |
| Q_{gd} | | | 62 | 85 | nC |
| R_{thJC} | | | | 0.50 | K/W |
| R_{thCK} | | | 0.15 | | K/W |

ISOPLUS 247 (IXFR) OUTLINE


| Dim. | Millimeter | | Inches | |
|----------------|------------|-------|----------|------|
| | Min. | Max. | Min. | Max. |
| A | 4.83 | 5.21 | .190 | .205 |
| A ₁ | 2.29 | 2.54 | .090 | .100 |
| A ₂ | 1.91 | 2.16 | .075 | .085 |
| b | 1.14 | 1.40 | .045 | .055 |
| b ₁ | 1.91 | 2.13 | .075 | .084 |
| b ₂ | 2.92 | 3.12 | .115 | .123 |
| C | 0.61 | 0.80 | .024 | .031 |
| D | 20.80 | 21.34 | .819 | .840 |
| E | 15.75 | 16.13 | .620 | .635 |
| e | 5.45 BSC | | .215 BSC | |
| L | 19.81 | 20.32 | .780 | .800 |
| L1 | 3.81 | 4.32 | .150 | .170 |
| Q | 5.59 | 6.20 | .220 | .244 |
| R | 4.32 | 4.83 | .170 | .190 |
| S | 13.21 | 13.72 | .520 | .540 |
| T | 15.75 | 16.26 | .620 | .640 |
| U | 1.65 | 3.03 | .065 | .080 |

| Source-Drain Diode | | Characteristic Values | | | |
|-----------------------|--|---|------|--------|--------|
| | | (T _J = 25°C, unless otherwise specified) | | | |
| Symbol | Test Conditions | min. | typ. | max. | |
| I_S | V _{GS} = 0 V | | | 26 A | |
| I_{SM} | Repetitive; pulse width limited by T _{JM} | | | 104 A | |
| V_{SD} | I _F = I _S , V _{GS} = 0 V, Note 1 | | | 1.5 V | |
| t_{rr} | I _F = I _S , -di/dt = 100 A/μs, V _R = 100 V | | | 250 ns | |
| Q_{RM} | | T _J = 25°C | | | 400 ns |
| | | T _J = 125°C | | | 1.5 μC |
| I_{RM} | | T _J = 25°C | | 10 | A |
| | T _J = 125°C | | 15 | A | |

- Note: 1. Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %
2. I_T test current: IXFR26N50 I_T = 13A
IXFR24N50 I_T = 12A
3. See IXFR26N50 data sheet for characteristic curves.